



STK22N6F3

N-channel 60 V, 0.0048 Ω , 22 A, PolarPAK[®]
STripFET[™] Power MOSFET

Preliminary Data

Features

Type	V _{DSS}	R _{DS(on)} max
STK22N6F3	60 V	< 0.006 Ω

- Ultra low top and bottom junction to case thermal resistance
- Extremely low on-resistance R_{DS(on)}
- Very low switching gate charge
- Fully encapsulated die
- 100% matte tin finish (in compliance with the 2002/95/EC european directive)
- High avalanche ruggedness
- PolarPAK[®] is a trademark of VISHAY

Application

- Switching applications

Description

This n-channel enhancement mode Power MOSFET is the latest refinement of ST's STripFET[™] process. The resulting transistor shows extremely high packing density for low on resistance, rugged avalanche characteristics and low gate charge.

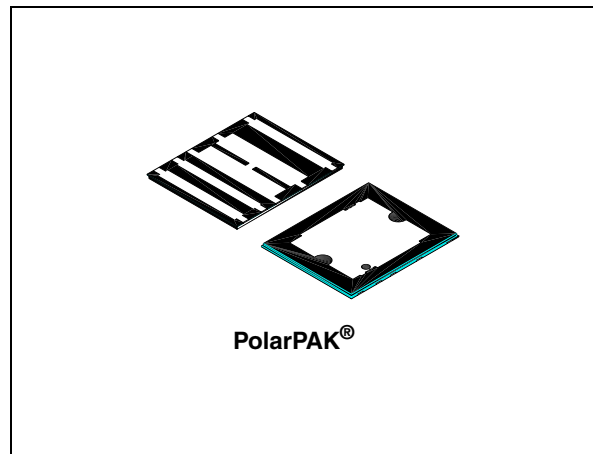


Figure 1. Internal schematic diagram

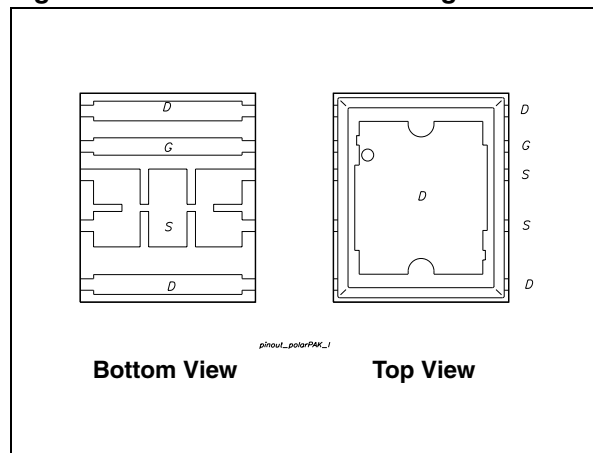


Table 1. Device summary

Order code	Marking	Package	Packaging
STK22N6F3	2263	PolarPAK [®]	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	60	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	22	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	13.7	A
$I_{DM}^{(2)}$	Drain current (pulsed)	88	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25^\circ\text{C}$	5.2	W
	Derating factor	0.0416	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	TBD	J
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. When mounted on FR-4 board of 1inch², 2 oz Cu and ≤ 10 sec
2. Pulse width limited by package
3. Starting $T_j = 25^\circ\text{C}$, $I_D = 11$ A, $V_{DD} = 48$ V

Table 3. Thermal data

Symbol	Parameter	Typ.	Max.	Unit
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb	20	24	$^\circ\text{C}/\text{W}$
$R_{thj-c}^{(2)}$	Thermal resistance junction-case (top drain)	0.8	1	$^\circ\text{C}/\text{W}$
$R_{thj-c}^{(3)}$	Thermal resistance junction-case (source)	2.2	2.7	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch², 2 oz Cu and ≤ 10 sec
2. Steady state
3. Measured at source pin when the device is mounted on FR-4 board in steady state

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	60			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating}, T_C = 125^{\circ}C$			10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 V, I_D = 11 A$		0.0048	0.006	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25 V, f = 1 \text{ MHz}, V_{GS} = 0$		2900		pF
C_{oss}	Output capacitance			554		pF
C_{rss}	Reverse transfer capacitance			20		pF
Q_g	Total gate charge	$V_{DD} = 48 V, I_D = 22 A$		50		nC
Q_{gs}	Gate-source charge	$V_{GS} = 10 V$		TBD		nC
Q_{gd}	Gate-drain charge	(see Figure 3)		TBD		nC
R_G	Gate input resistance	f=1 MHz Gate DC Bias = 0 Test signal level = 20 mV open drain		TBD		Ω

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD}=48\text{ V}$, $I_D=11\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 2)		TBD TBD		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD}=48\text{ V}$, $I_D=11\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 2)		TBD TBD		ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				22 88	A A
$V_{SD}^{(2)}$	Forward on Voltage	$I_{SD}=22\text{ A}$, $V_{GS}=0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=22\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=48\text{ V}$, $T_j=150^\circ\text{C}$ (see Figure 7)		TBD TBD TBD		ns nC A

1. Pulse width limited by package
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

3 Test circuits

Figure 2. Switching times test circuit for resistive load

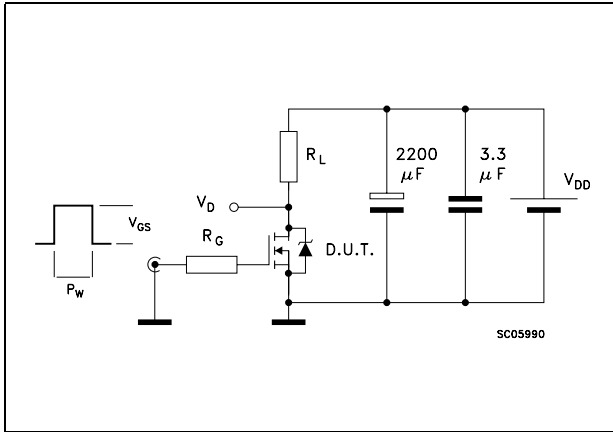


Figure 3. Gate charge test circuit

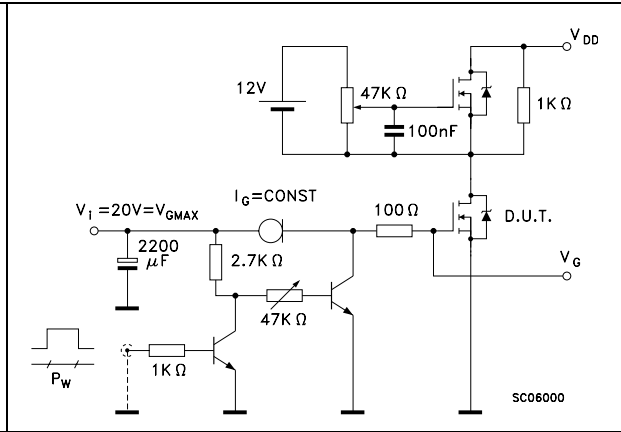


Figure 4. Test circuit for inductive load switching and diode recovery times

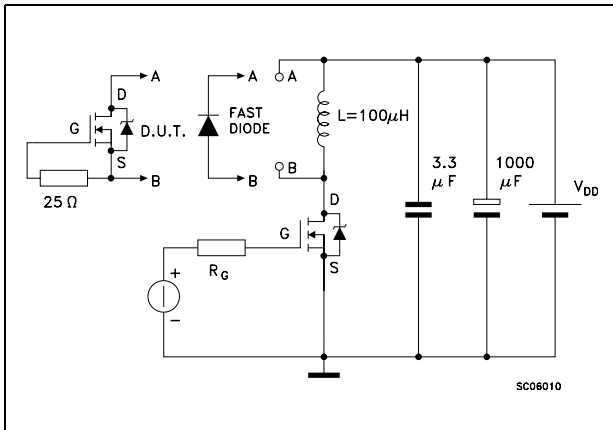


Figure 5. Unclamped inductive load test circuit

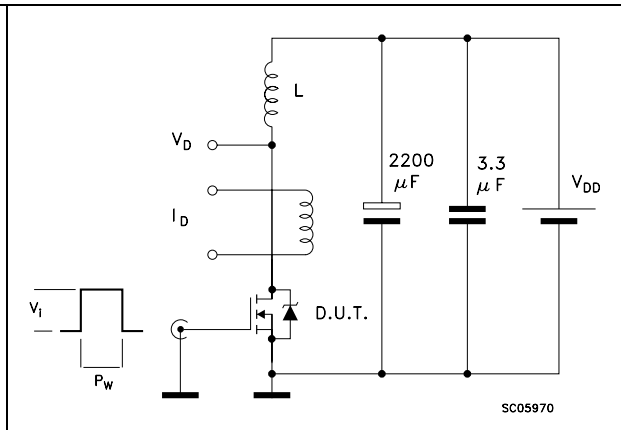


Figure 6. Unclamped inductive waveform

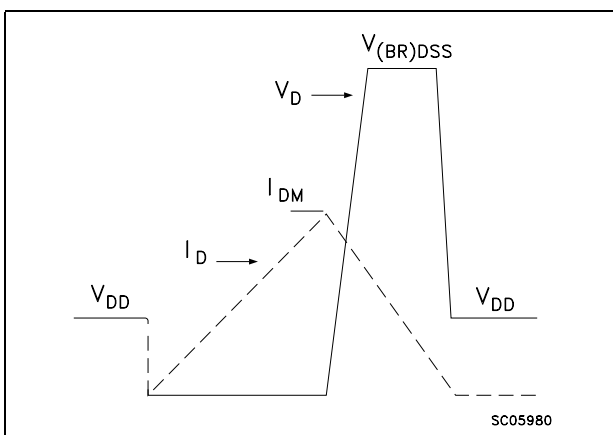


Figure 7. Switching time waveform

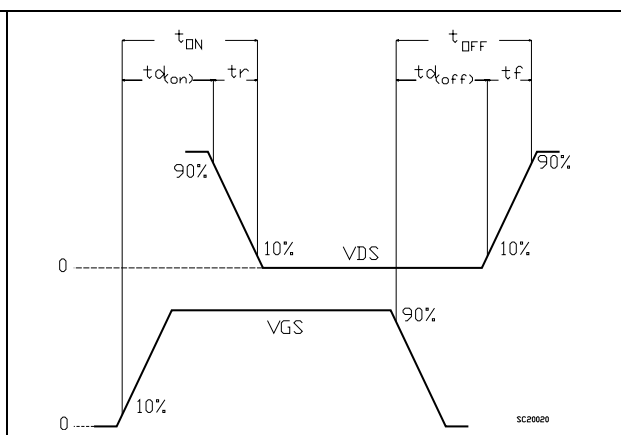
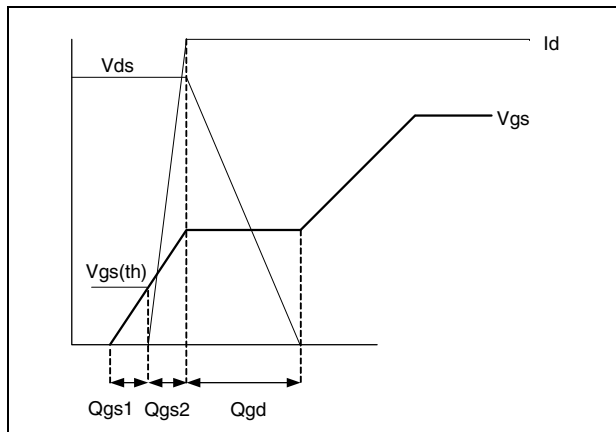


Figure 8. Gate charge waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Table 8. PolarPAK® (option “L”) mechanical data

Ref.	mm			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.75	0.80	0.85	0.030	0.031	0.033
A1			0.05			0.002
b1	0.48	0.58	0.68	0.019	0.023	0.027
b2	0.41	0.51	0.61	0.016	0.020	0.024
b3	2.19	2.29	2.39	0.086	0.090	0.094
b4	0.89	1.04	1.19	0.035	0.041	0.047
b5	0.23	0.33	0.43	0.009	0.013	0.017
c	0.20	0.25	0.30	0.008	0.010	0.012
D	6	6.15	6.30	0.236	0.242	0.248
D1	5.74	5.89	6.04	0.226	0.232	0.238
E	5.01	5.16	5.31	0.197	0.203	0.209
E1	4.75	4.90	5.05	0.187	0.193	0.199
H1	0.23			0.009		
H2	0.45		0.56	0.018		0.022
H3	0.31	0.41	0.51	0.012	0.016	0.020
H4	0.45		0.56	0.018		0.022
K1	4.22	4.37	4.52	0.166	0.172	0.178
K2	1.08	1.13	1.18	0.043	0.044	0.046
K3	1.37			0.054		
K4	0.24			0.009		
M1	4.30	4.50	4.70	0.169	0.177	0.185
M2	3.43	3.58	3.73	0.135	0.141	0.147
M3	0.22			0.009		
M4	0.05			0.002		
P1	0.15	0.20	0.25	0.006	0.008	0.010
T1	3.48	3.64	4.10	0.137	0.143	0.161
T2	0.56	0.76	0.95	0.022	0.030	0.037
T3	1.20			0.047		
T4	3.90			0.154		
T5		0.18	0.36		0.007	0.014
<	0°	10°	12°	0°	10°	12°

Figure 9. PolarPAK® (option "L") drawings

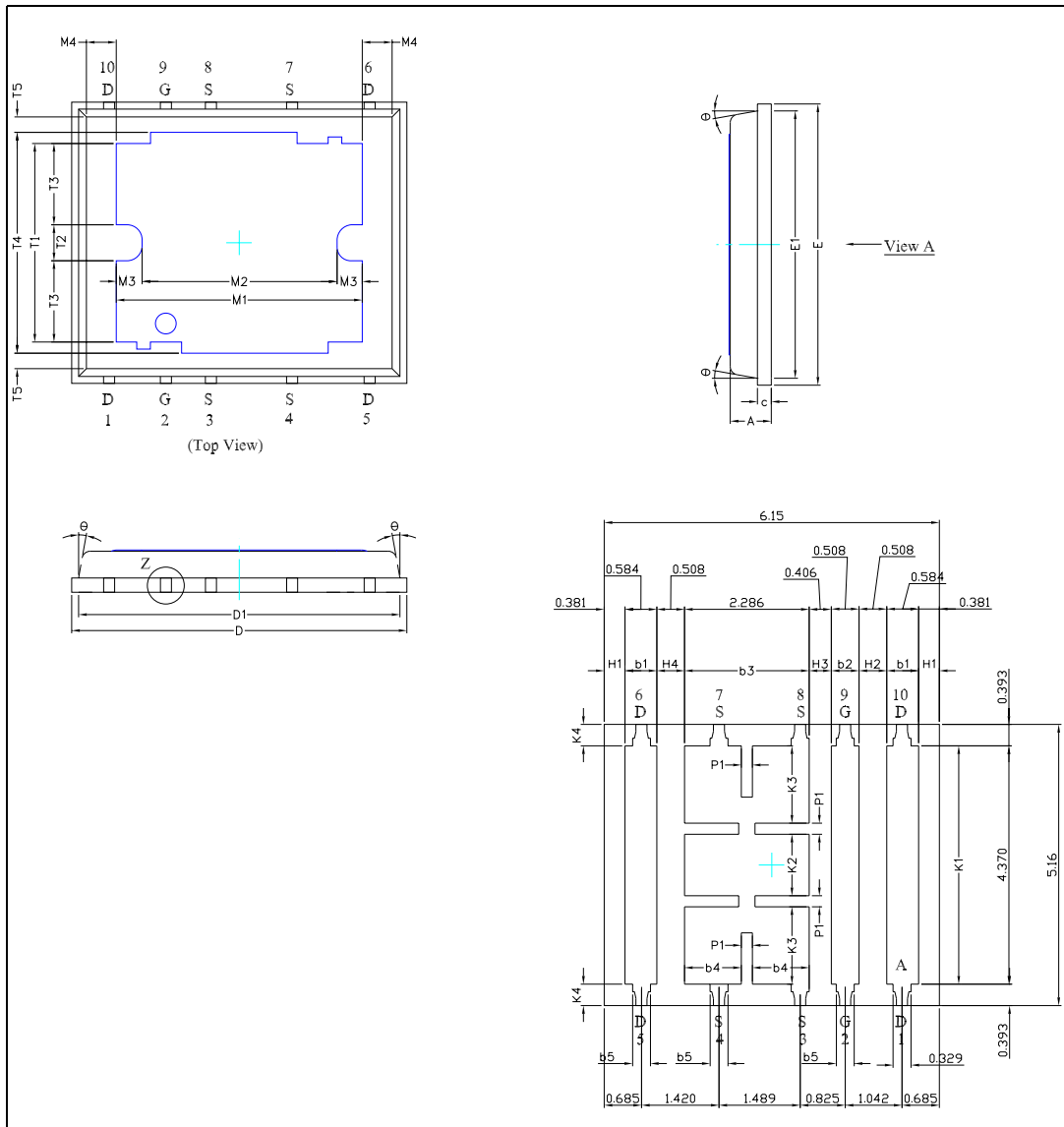
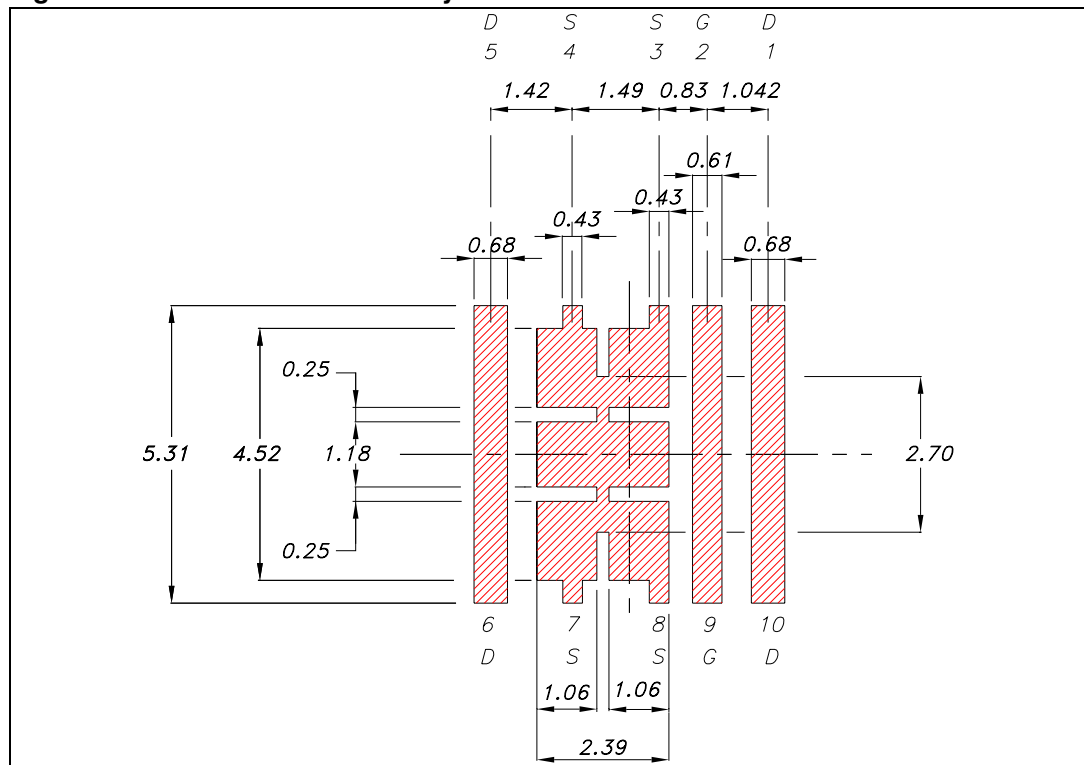


Figure 10. Recommended PAD layout



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
01-Jul-2008	1	First release

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